

Radiation	Type	Technology	Electrodes
Infrared	MQW	InGaAs/GaAs	N (cathode) up

	typ. dimensions (μm)	
	<u>typ. thickness</u> 260 (±20) μm  <u>cathode</u> gold alloy, 1.5 μm  <u>anode</u> gold alloy, 1.5 μm, solderable	

**Optical and Electrical Characteristics**

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> = 100 mA	V <sub>F</sub>		1.2	1.4	V
Reverse voltage	I <sub>R</sub> = 10 μA	V <sub>R</sub>	10			V
Radiant power <sup>1</sup>	I <sub>F</sub> = 100 mA	Φ <sub>e</sub>	0.75	1.5		mW
Radiant power <sup>2</sup>	I <sub>F</sub> = 100 mA	Φ <sub>e</sub>		3.0		mW
Peak wavelength	I <sub>F</sub> = 100 mA	λ <sub>p</sub>	1000	1020	1050	nm
Spectral bandwidth at 50%	I <sub>F</sub> = 100 mA	Δλ <sub>0.5</sub>		80		nm
Switching time	I <sub>F</sub> = 100 mA	t <sub>r</sub> , t <sub>f</sub>		10		ns

<sup>1</sup>Measured on bare chip on TO-18 header with *EPIGAP* equipment

<sup>2</sup>Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

**Labeling**

Type	Lot N°	Φ <sub>e</sub> (typ) [mW]	V <sub>F</sub> (typ) [V]	Quantity
ELC-1020-28-1				

**Packing:** Chips on adhesive film with wire-bond side on top